

Swiss participation in AIDAinnova



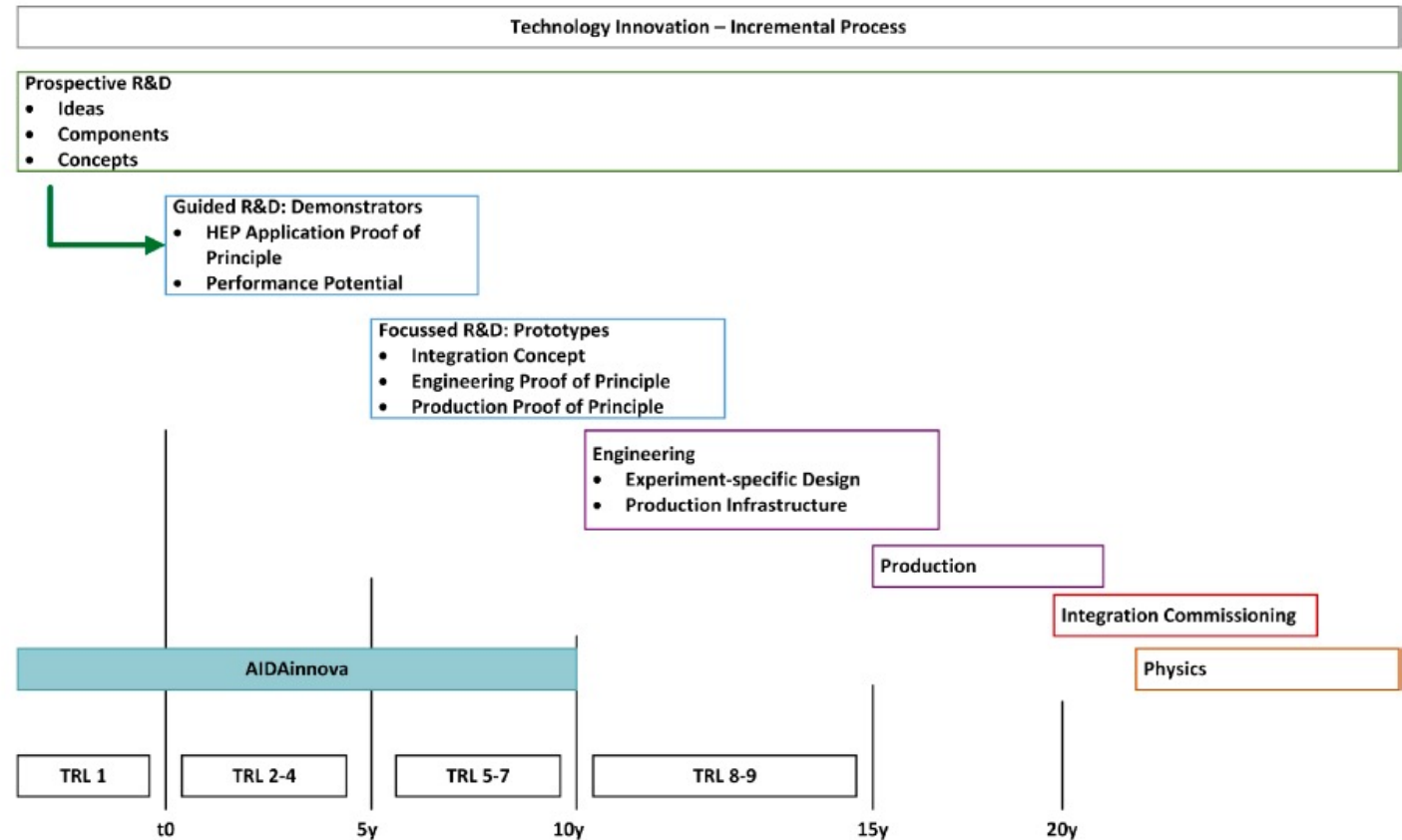
This project has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreement No 101004761.

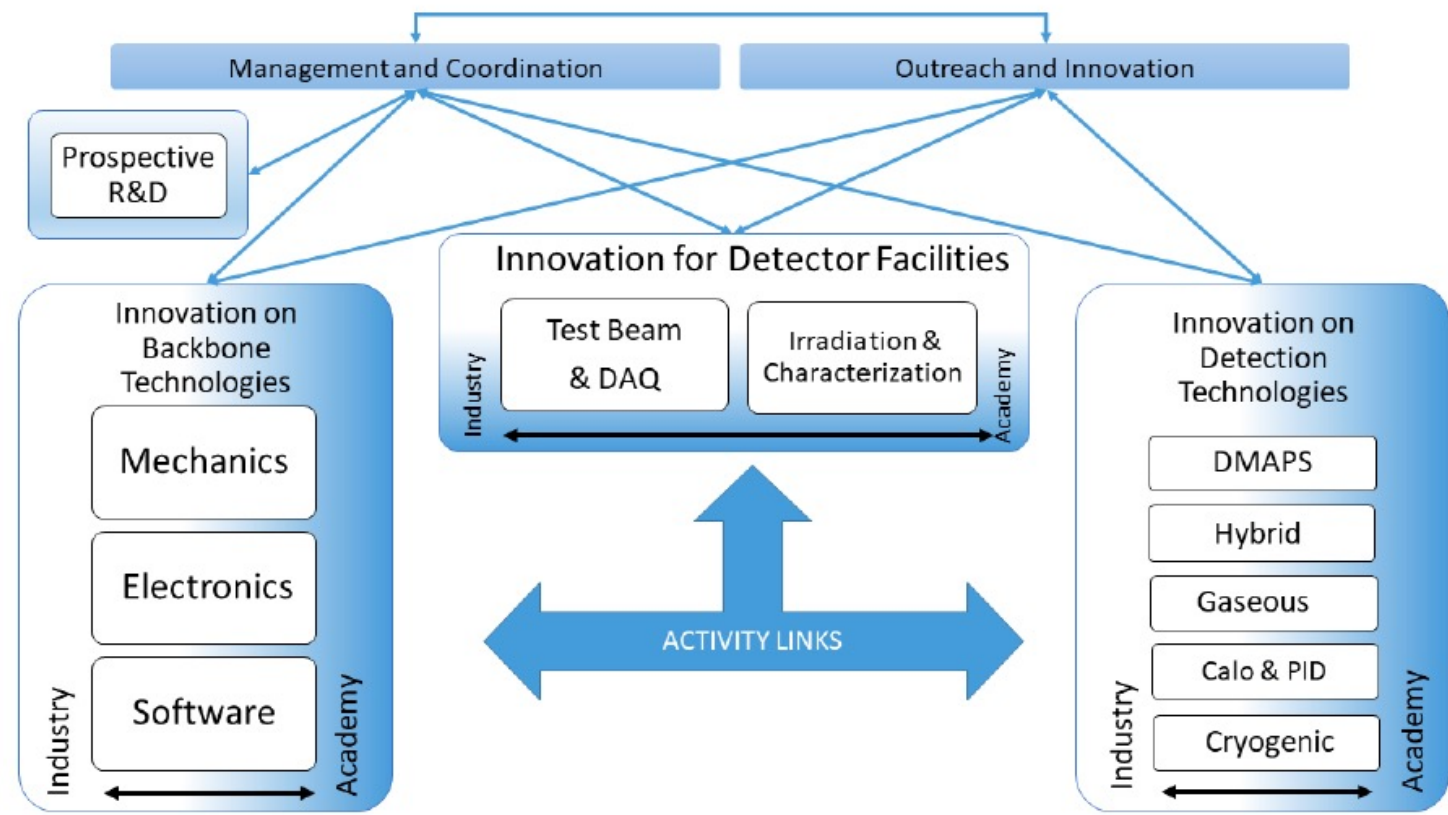
AIDAinnova focusses on Strategic R&D in the pre-TDR phase

- Technology Readiness Levels 2-7
- Not yet experiment-specific: potential to unfold synergies **Include some prospective R&D**
- competitive call at start of project • “Blue Sky”, quantum sensors,...

Targeted applications

- Higgs Factories
- ALICE, LHCb LS3 pre-TDR, ATLAS & CMS LS4
- Accelerator-based neutrino experiments
- and others





Similarities with

- AIDA-2020
- CERN Detector R&D
- ECFA Detector Roadmap



DMAPS development

High rate & radiation:
radhard (TID & NIEL) + fast resp. time + fast R/O
example: LHC upgrades & FCC

High granularity:
excellent spatial resolution + (fast + radhard):
ex.: Belle II upgrade & future Higgs factory etc.

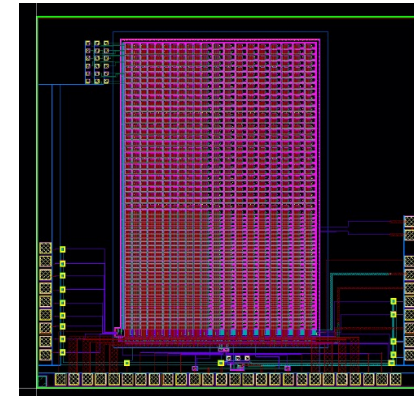
concrete development lines

Foundry line	chips dev. line	charge coll.	high rate & radiation	high granularity	special aim
LFoundry 150 nm	LF-Monopix2	large electrode	X		radhard, robust
LFoundry 150 nm	LF-MPW3/4	large electrode	X	(X)	small pixels
TowerJazz 180 nm	TJ-Monopix2/3	small electrode	(X)	X	Belle II Upgrade
TowerJazz 180 nm	TJ-MALTA2/3	small electrode	X	(X)	low power
LFoundry 110 nm	ARCADIA	small electrode		X	large area, low power
TowerJazz 65 nm	TJ 65	tbd ... likely small		X	small feature size

WP5 convenors: Sebastian Grinstein (IFAE Barcelona), David-Leon Pohl, NW (Univ. of Bonn)

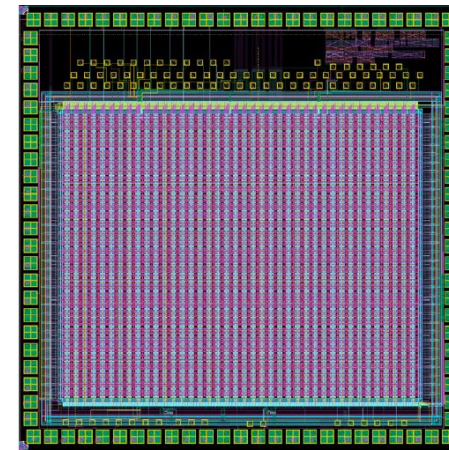


- PSI is partner organization in AIDAinnova – WP5: Depleted Monolithic Active Pixel Sensors
- Development of radiation tolerant Depleted Monolithic Active Pixel Sensors (DMAPS) for high-rate applications
 - in close collaboration with ETH and UZH
- For future upgrades of the CMS experiment, future collider experiments, in-house experiments and other applications
- Effort started in 2018
- Evaluated different technologies, now following up two ([TSI](#) and [Lfoundry110](#)) with own submissions
- More information in this [Tilman Rohe's talk](#)



Pixel chip in TSI prototype run:

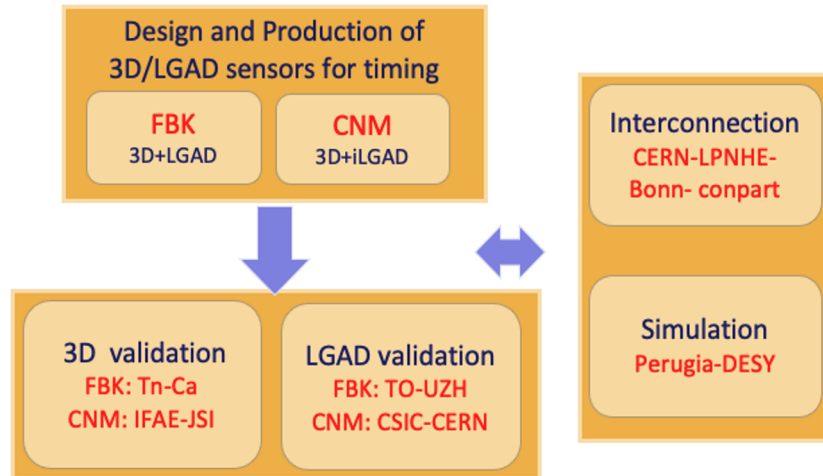
- 4 different pixel sizes
- Discriminator in each pixel with 3 trim bits
- External hold possible (as in R4S chip)



Motic A: Monolithic timing chip

- LF110 nm with back-side implant
- Pulse height and time of arrival is measured
- 5x5 mm² chip with different preamplifier designs

WP6 Work Plan



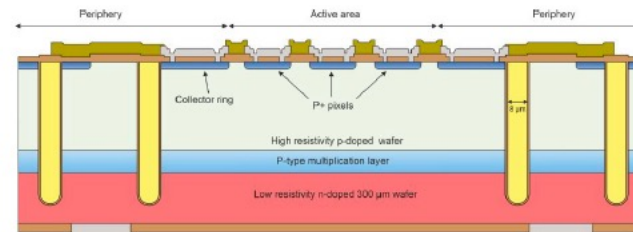
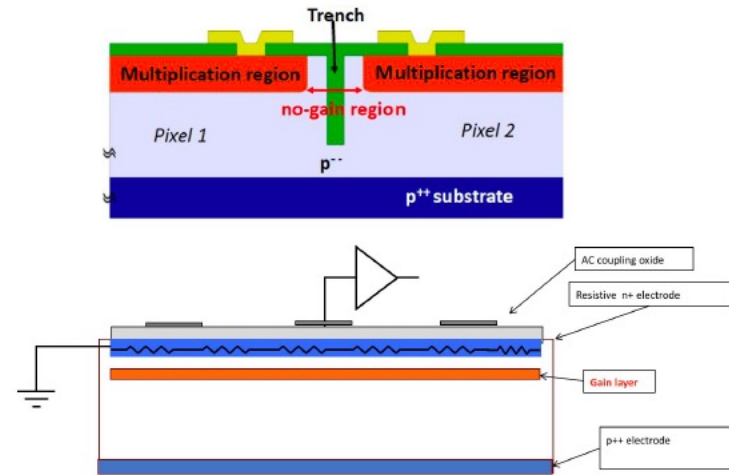
Timing applications @ FCC

- 4D Tracking and pile-up mitigation at FCC-hh
- Potential applications at FCC-ee:
 - Interest for use as a PID detector
 - Search for long-lived particles
 - Studies of the characteristics of events from different regions of the interacting bunches

Low Gain Avalanche Diode (LGAD) detectors proposed for timing applications: upgrades of Endcap timing layer in CMS and High Granularity Timing Detector in ATLAS.

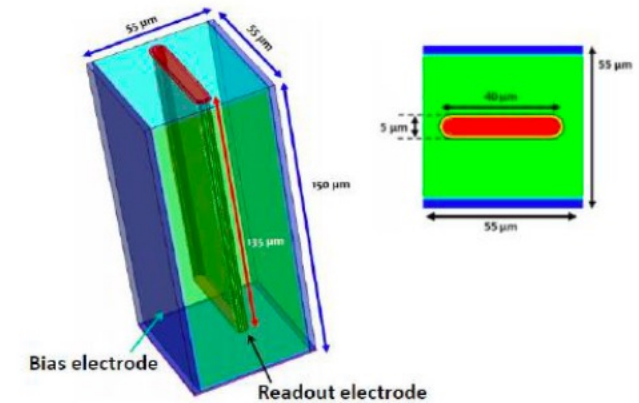
- In WP6 pushing for higher segmentation and rad-hardness.

- LGADs with Trench-Isolated trenches (TI-LGAD)
- Resistive AC-Coupled Silicon Detectors (RSD)
 - AC-pad coupled to the resistive n+ via dielectric coupling layer
 - Not segmented gain layer: 100% fill factor
 - Radiation hardness to be evaluated



- Inverse LGAD (iLGAD):
 - multiplication region on the opposite side of the read-out electrodes

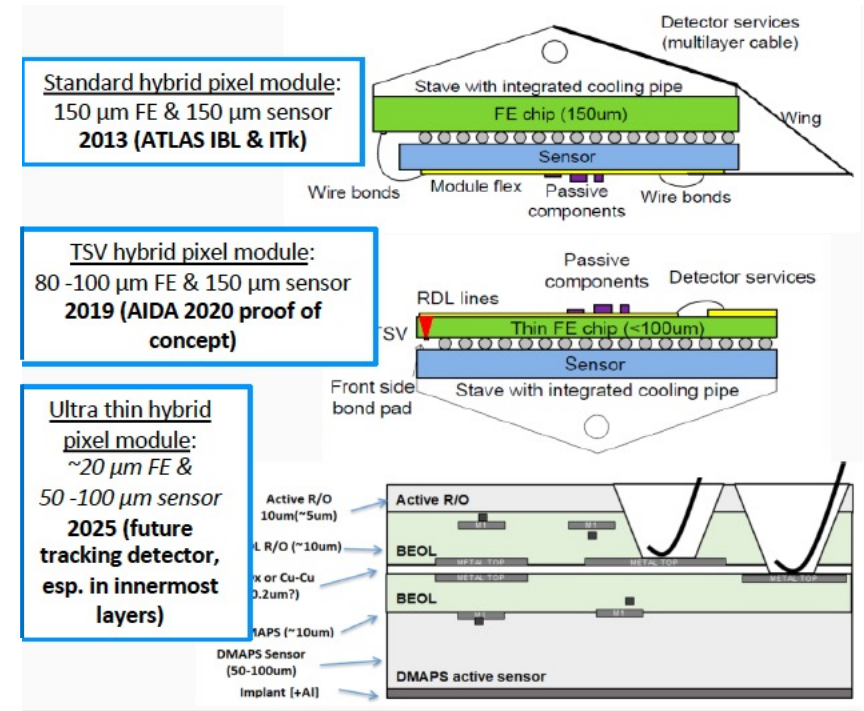
3D pixels for timing



The idea is to use a 3D based on trenches instead of columns in order to obtain a more uniform electric/weighting field between electrodes → reduction of the dependence of timing on the impact position of particles

Goal: reduce mass, i.e. thickness of pixel detectors as much as possible while keeping the benefits of the hybrid approach:

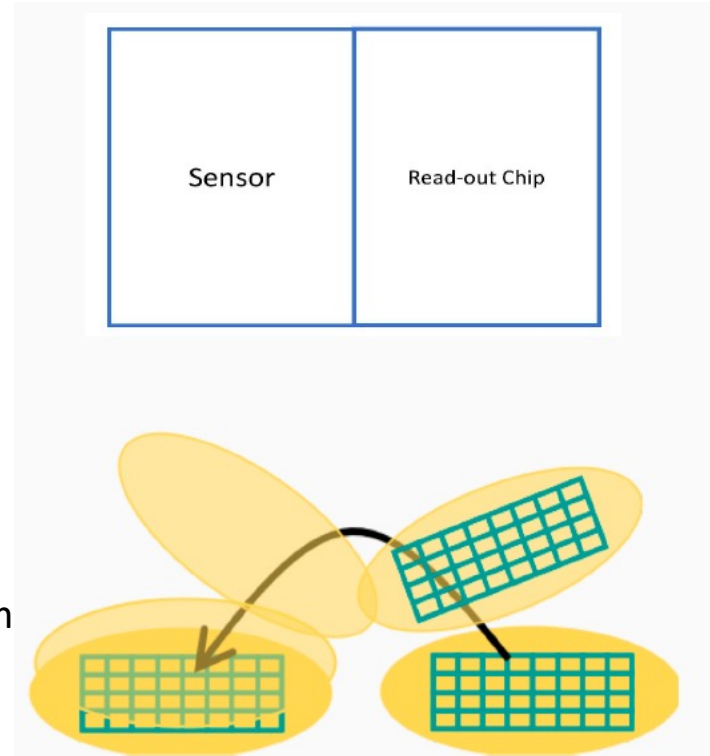
- Separate development and optimization of sensors and FE electronics allowing for best performance of FE electronic and sensor.
- Fine pitch interconnection between FE and sensor pixel with about **20 μm pitch**.
- Thinning of FE and sensor parts to the minimum. Target is the development of ultra-thin hybrid pixel detectors based on:
 - **50 – 100 μm thick pixel sensor on 200 (300) mm CMOS wafers**
 - **$\sim 20 \mu\text{m}$ thick pixel FE chip thickness on 200 (300) mm CMOS**



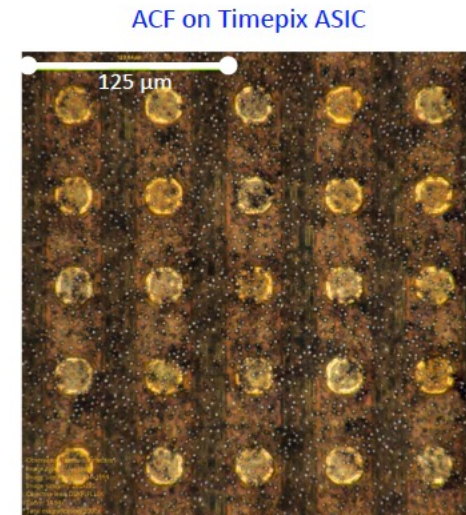
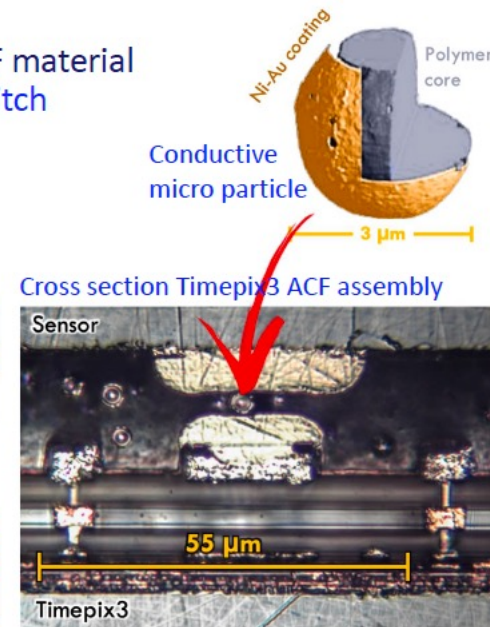
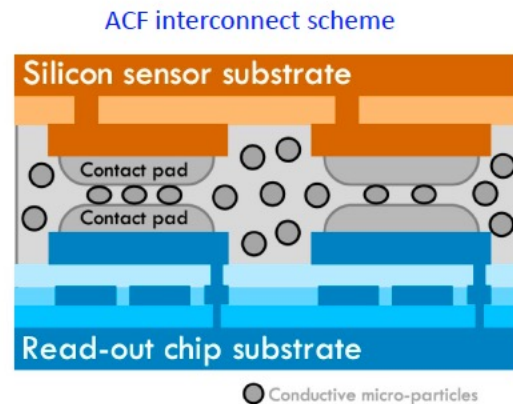
Bonn Uni and IZM

Develop dedicated CMOS Sensor wafer compatible with a pixel FE chip wafer:

- Starting point: [passive CMOS sensor](#) development on 200 mm wafer with 110/150 nm process node from Lfoundry
- Use either [TimePix3 chip wafers](#) (130 nm on 200 mm wafers) or own [FE development](#) on the same wafer as the sensor
- Develop and optimize hybridization process including thinning and interconnection from chip's backside
- Transfer process to more modern feature size pixel chips (65nm or 28 nm on 300 mm wafers) for smaller pixel pitches and faster electronics (long term, not with AIDAInnova)



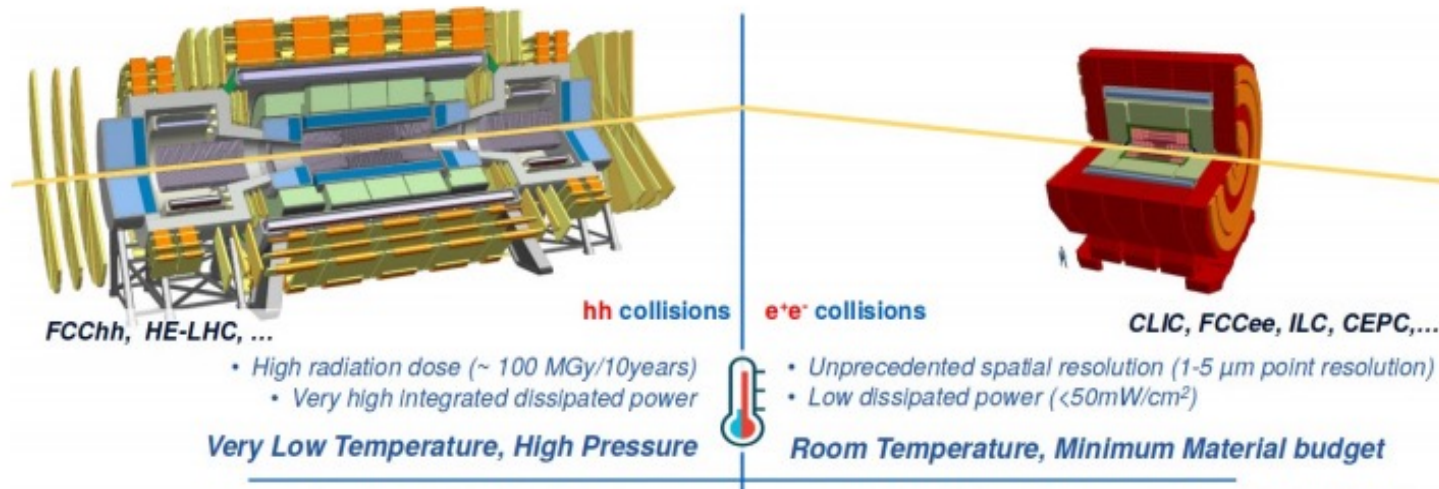
- Bump bonding in specialized industry is costly / complex
- Alternative process: Anisotropic Conductive Films (ACF)
 - Epoxy film for mechanical connection, embedded conductive particles for el. connection
 - Mask-less sensor/ASIC metallization: Electroless Nickel Gold (ENIG) deposition
 - In-house flip-chip process
 - Challenge: Optimization of ACF material and flip-chip process for fine pitch



Involved groups:

- CERN: Sample preparation (metallisation), flip-chip detector assembly, testing, process optimization
- Conpart: Industrial partner / ACF supplier, R&D on micro particles, ACF characterisation, process optimization
- CNRS-LPNHE: Sensor and test-structure procurement and production, testing
- Outside AidaInnova: DESY (test beam) and Geneva (Support for flip-chip infrastructure)

- Bring to maturity CMOS-compatible Si- μ -channel fab processes
- Exploit additive manufacturing for
 - Ultra-thin metal cooling devices
 - Ceramic (composites?) cooling devices
 - Hydraulic connections and interconnections
- Ultra light structures integrating cooling features
- New approach to (natural) refrigerant fluids for warm and cold applications
- Develop instrumentation for accurate absolute position measurements on very small devices

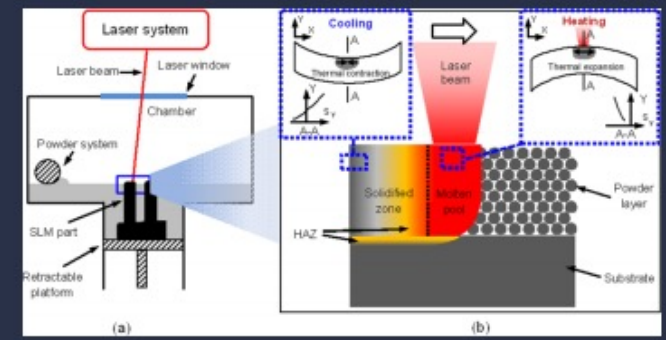



Ultra light 3D printed cold plates @CSEM

- Additive Manufacturing technologies (“3D-printing”):
- standardised and reliable approaches to produce 3D-printed high precision micro-channel cold plates.
- Study Different metallic alloys and ceramic composites
- Investigate the minimum channel cross section attainable for a fixed channel length
- Guidelines toward engineering of the future advanced detector cooling solutions.

- Top Swiss RTO* with strong background (among others) in high precision manufacturing.
- Involved: Additive Manufacturing & Component Reliability group
- Specialist of metal printing

- Laser powder based process
- Minimum size 60-150µm, material dependent
- Minimum gap ~100µm
- Material available/underdevelopment:
 - Stainless steel: 316L, 17-4PH
 - Titanium alloys: Ti-6Al-4V, NiTi (shape memory)
 - Copper based: CuSn10
 - Aluminum based: AlSi12, Scalmalloy
 - INVAR (Fe64Ni36) → Kovar (?)
 - Metal Matrix Composite


Additional material



Another call in FP8 was not obvious

- Followed intensive discussions with EC, incl. actions by the CERN directorate



Targeted Call INFRAINNOV-04-2020: Innovation pilots

- Addressing advanced Integrated Activities (i.e. the AIDA-2020 community)
- which have reached a high level of integration and can focus on joint research: **collaborative**

Objectives

- Support research **infrastructure** networks developing and implementing a **common strategy/roadmap** including technological development required for improving their services through **partnership with industry**
- Support **incremental innovation** and cooperation with industry

Complementarity to ATTRACT (competitive, disruptive)

Increased focus on industrial partners

No Transnational Access

infrastructure:
common interest



Proposed funding 10 M€ for 4 years

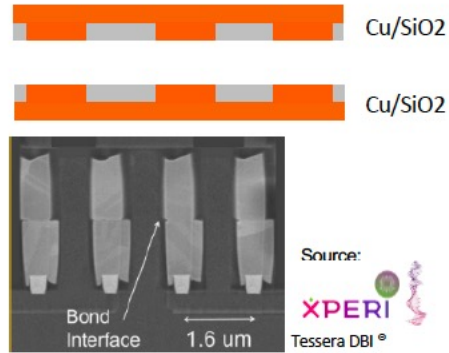
Felix Sefkow | April 2021

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Metal – Oxide Hybrid Bonding



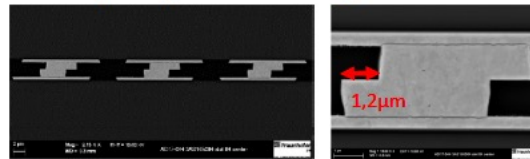
Process:

- SiO₂ passivation + Cu pads
- Surface planarization (CMP)
- Surface activation (plasma, chemicals)
- Room temperature bond
- Annealing 150 – 300°C
- 3D chip stacking: memory chips, image sensors

Motivation for DBI[®]:

- W2W , D2W
- Highest interconnect density: I/O pitch down to 1 μm
- High alignment accuracy
- No bumps, no intermetallics
- No gap – no underfilling
- High reliability

Fraunhofer IZM-ASSID: 300mm W2W Bonding with <5μm alignment accuracy

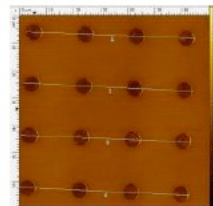


J. Wolf „3D System Integration Requirements and Potential Solutions“, European 3D Summit, 22-24.1.2018, Dresden, Germany.

© Fraunhofer IZM

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Fraunhofer test chip with 4 μm pad /18μm pitch, Metal density: 4.5%



	FhG IZM ASSID (Results)
Roughness beside TSV (Oxide) Ra	0,146 nm
Roughness on TSV (Cu) Ra	0,163 nm
Planarization	5nm @ 100μm

Surface preparation in nanometer range → Atomic force microscopy